

Phase Transformation of Materials

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Contents for previous class

- Binary phase diagrams 각 온도의 G-X 관계 도식 ↔ T-X 관계 도식으로 plot 합금의 평형조성 → 주어진 온도에서 얻은 자유에너지 곡선으로 얻음 평형은 온도변화에 따라 어떻게 변화되어 가는가?

- 1) Simple Phase Diagrams
- 2) Systems with miscibility gap
- 4) Simple Eutectic Systems
- 3) Ordered Alloys
- 5) Phase diagrams containing intermediate phases
- Gibbs Phase Rule F = C P + 2 (from T, P)

Contents for today's class

- Effect of Temperature on Solid Solubility
- Equilibrium Vacancy Concentration
- Influence of Interfaces on Equilibrium
- Ternary Equilibrium: Ternary Phase Diagram

Effect of T on solid solubility





Q: heat absorbed (enthalpy) when 1 mole of β dissolves in A rich α as a dilute solution.

Equilibrium Vacancy Concentration $\Delta G = \Delta H - T \Delta S$

• Vacancies increase the internal energy of crystalline metal due to broken bonds formation.

$$\Delta H \cong \Delta H_V X_V$$

- Vacancies increase entropy because they change the thermal vibration frequency and also the configurational entropy.
- Total entropy change is thus

$$\Delta S = \Delta S_{v} X_{v} - R\{X_{v} \ln X_{v} + (1 - X_{v}) \ln(1 - X_{v})\}$$

The molar free energy of the crystal containing X_v mol of vacancies $G = G_A + \Delta G = G_A + \Delta H_v X_v - T\Delta S_v X_v + RT\{X_v \ln X_v + (1 - X_v) \ln(1 - X_v)\}$

> With this information, estimate the equilibrium vacancy concentration.

at equilibrium
$$\left(\frac{dG}{dX_V}\right)_{X_V = X_V^e}$$

 $\Delta H_V - T\Delta S_V + RT \ln X_V^e = 0$
 $X_V^e = exp \frac{\Delta S_V}{R} \cdot exp \frac{-\Delta H_V}{RT}$
putting $\Delta G_V = \Delta H_V - T\Delta S_V$
 $X_V^e = exp \frac{-\Delta G_V}{RT}$

= 0

 In practice, △H_v is of the order of 1 eV per atom and X_v^e reaches a value of about 10⁻⁴~10⁻³ at the melting point of the solid



Fig. 1.37 Equilibrium vacancy concentration.

Interface $(\alpha/\beta)=\gamma$





Fig. 1.38 The effect of interfacial energy on the solubility of small particles.

 $\Delta G = \frac{2\gamma V_m}{2} \quad \text{of effect}$ r

Gibbs-Thomson effect: 계면에너지로 인해 자유에너지가 증가하는 현상

$$X_{B}^{e} = \exp(-\frac{\Delta G_{B} + \Omega}{RT})$$

$$X_{B}^{r=\infty} = \exp(-\frac{\Delta G_{B} + \Omega}{RT})$$

$$X_{B}^{r=r} = \exp(-\frac{\Delta G_{B} + \Omega - 2\gamma V_{m} / r}{RT})$$

$$= X_{B}^{r=\infty} \exp(\frac{2\gamma V_{m}}{RTr})$$

$$\frac{X_{B}^{r=r}}{X_{B}^{r=\infty}} = \exp(\frac{2\gamma V_{m}}{RTr}) \approx 1 + \frac{2\gamma V_{m}}{RTr}$$
Ex) $\gamma = 200 \text{mJ/m}^{2}$, $V_{m} = 10^{-5} \text{ m}^{3}$, $T = 500 \text{K}$

$$\frac{X_{r}}{X_{\infty}} = 1 + \frac{1}{r(nm)}$$

r=10nm 이면 10% 증가

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Fig. 1.39 Transfer of dn mol of β from large to a small particle.

 β formation in α

 β Nucleation & growth in α

Interface (α/β) : size barrier composition barrier

Undercooling이 클수록 **r***가 작다

→ Nucleation ↑β 상의 수

 \rightarrow size barrier (r*)

Additional Thermodynamic Relationships for Binary Solutions ➡ 조성 변화로 인한 화학퍼텐셜의 변화 계산: Gibbs-Duhem 식



The Gibbs-Duhem Equation

be able to calculate the change in chemical potential ($d\mu$) that result from a change in alloy composition (dX).

For a regular solution,

$$G = X_A G_A + X_B G_B + \Omega X_A X_B + RT(X_A \ln X_A + X_B \ln X_B)$$
$$\frac{d^2 G}{dX^2} = \frac{RT}{X_A X_B} - 2\Omega$$
$$d^2 G RT$$

For a ideal solution, $\Omega = 0$,

$$\frac{d^2 G}{dX^2} = \frac{RT}{X_A X_B}$$

$$\mu_{\rm B} = \mathbf{G}_{\rm B} + \mathbf{RT} \ln \mathbf{a}_{\rm B} = \mathbf{G}_{\rm B} + \mathbf{RT} \ln \gamma_{\rm B} \mathbf{X}_{\rm B}$$
$$\frac{d\,\mu_{B}}{dX_{B}} = \frac{RT}{X_{B}} \left\{ 1 + \frac{X_{B}}{\gamma_{B}} \frac{d\,\gamma_{B}}{dX_{B}} \right\} = \frac{RT}{X_{B}} \left\{ 1 + \frac{d\,\ln\gamma_{B}}{d\,\ln X_{B}} \right\}$$

a similar relationship can be derived for $d\mu_A/dX_B$

$$-X_A d\mu_A = X_B d\mu_B = RT \left\{ 1 + \frac{d \ln \gamma_A}{d \ln X_A} \right\} dX_B = RT \left\{ 1 + \frac{d \ln \gamma_B}{d \ln X_B} \right\} dX_B$$

$$-X_A d\mu_A = X_B d\mu_B = X_A X_B \frac{d^2 G}{dX^2} dX_B$$

$$X_A X_B \frac{d^2 G}{dX^2} = RT \left\{ 1 + \frac{d \ln \gamma_A}{d \ln X_A} \right\} = RT \left\{ 1 + \frac{d \ln \gamma_B}{d \ln X_B} \right\}$$

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Driving force: precipitation

- * Consider the chemical potential of component *B* in phase *alpha* compared to *B* in *beta*. This difference, labeled as ΔG_n on the right of the lower diagram is the driving force (expressed as energy per mole, in this case).
- * To convert to *energy/volume*, divide by the molar volume for *beta*: $\Delta G_V = \Delta G_n / V_m$.

Driving force for the reaction : ΔG_0

Driving force for nucleation : ΔG_n

Because the first nuclei of beta to appear do not ignificantly change the composition of the parent material



Fig. 5.3 Free energy changes during precipitation. The driving force for the first precipitates to nucleate is $\Delta G_n = \Delta G_v V_m$. ΔG_0 is the total decrease in free energy when precipitation is complete and equilibrium has been reached.



What are ternary phase diagram?

Diagrams that represent the equilibrium between the various phases that are formed between three components, as a function of temperature.

Normally, pressure is not a viable variable in ternary phase diagram construction, and is therefore held constant at 1 atm. **Gibbs Phase Rule for 3-component Systems**

F = C + 2 - P For isobaric systems: F = C + 1 - P

For C = 3, the maximum number of phases will co-exist when F = 0

$$P = 4$$
 when $C = 3$ and $F = 0$

Components are "independent components"

Gibbs Triangle

An Equilateral triangle on which the pure

components are represented by each corner.



Concentration can be expressed as either "wt. %" or "at.% = molar %".

 $X_{A}+X_{B}+X_{C}=1$

Used to determine the overall composition

Overall Composition



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Overall Composition



Isomorphous System: A system (ternary in this case) that has only one solid phase. All components are totally soluble in the other components. The ternary system is therefore made up of three binaries that exhibit total solid solubility

<u>The Liquidus Surface</u>: A plot of the temperatures above which a homogeneous liquid forms for any given overall composition

The Solidus Surface: A plot of the temperatures below which a (homogeneous) solid phase forms for any given overall composition





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Isothermal section \rightarrow F = C - P



Isothermal section



Isothermal section \rightarrow F = C - P



solid phases of a ternary system.

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Locate overall composition using Gibbs triangle



<u>Tie line</u>: A straight line joining any two ternary compositions

Amount of each phase present is determined by using the Inverse Lever Rule

5. Fraction of solid = YX/YZ

6. Fraction of liquid = ZX/YZ

Ternary Eutectic System – No Solid Solubility

The Ternary Eutectic Reaction:

$$\mathsf{L} = \alpha + \beta + \gamma$$

A liquid phase solidifies into three separate solid phases

Made up of three binary eutectic systems, all of which exhibit no solid solubility

Ternary Eutectic System





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T= ternary eutectic temp.



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- TA: Melting Point Of Material A
- T_B: Melting Point Of Material B
- T_C: Melting Point Of Material C
- TEI: Eutectic Temperature Of A-B
- T_{E2}: Eutectic Temperature Of B-C
- TE3: Eutectic Temperature Of C-A





Main outline of Ternary Phase Diagram with Ternary Eutectic (Te) and Solid Single Phase Regions Shown











T= ternary eutectic temp.





http://www.youtube.com/watch?v=yzhVomAdetM

Ternary Eutectic System

Solidification Sequence



Ternary Eutectic System

Solidification Sequence



2 상영역에서 주직 단면이 tie line과 물일 치하므로 다른 온도에서 평형상만 나타내 고 조성은 표시할 수 없음.

Quarternary의 평형상태를 기하학적으로 표시한 그림

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4성분원소들 가운데서 임의의 3성분의 농도가 독립적으로 변할 수 있는 함수이 므로 여러가지 조성의 Quar-ternary alloy은 공간적으로 표시된다. 3원계의 조성은 정4면체의 면상에, 그리고 4원계 합금의 조성은 정4면체의 내부공간에 표시된다. 합금의 조성은 정4면체의 기 하학적성질에 의하여 결정된다. 4원계 에서 상조성을 결정하기 위하여 lever rule을 이용한다. 4원합금의 변태과정을 고찰할 때 정4면체안의 추상적인 4차원 투영을 이용한다.

